

DATA SHEET

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74AHC2G00; 74AHCT2G00 2-input NAND gate

Product specification

2004 Jan 21

2-input NAND gate

74AHC2G00; 74AHCT2G00

FEATURES

- Symmetrical output impedance
- High noise immunity
- ESD protection:
 - HBM EIA/JESD22-A114-A exceeds 2000 V
 - MM EIA/JESD22-A115-A exceeds 200 V
 - CDM EIA/JESD22-C101 exceeds 500 V.
- Low power dissipation
- Balanced propagation delays
- SOT505-2 and SOT765-1 package
- Specified from –40 to +85 °C and –40 to +125 °C.

DESCRIPTION

The 74AHC2G/AHCT2G00 is a high-speed Si-gate CMOS device.

The 74AHC2G/AHCT2G00 provides the 2-input NAND gate function.

QUICK REFERENCE DATA

GND = 0 V; $T_{amb} = 25\text{ °C}$; $t_r = t_f \leq 3.0\text{ ns}$.

SYMBOL	PARAMETER	CONDITIONS	TYPICAL		UNIT
			AHC2G	AHCT2G	
t_{PHL}/t_{PLH}	propagation delay nA and nB to nY	$C_L = 15\text{ pF}$; $V_{CC} = 5\text{ V}$	3.5	3.6	ns
C_I	input capacitance		1.5	1.5	pF
C_{PD}	power dissipation capacitance per gate	$C_L = 50\text{ pF}$; $f = 1\text{ MHz}$; notes 1 and 2	17	18	pF

Notes

1. C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

$$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o) \text{ where:}$$

f_i = input frequency in MHz;

f_o = output frequency in MHz;

C_L = output load capacitance in pF;

V_{CC} = supply voltage in Volts;

N = total load switching outputs;

$\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.

2. The condition is $V_I = \text{GND to } V_{CC}$.

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FUNCTION TABLE

See note 1.

INPUT		OUTPUT
nA	nB	nY
L	L	H
L	H	H
H	L	H
H	H	L

Note

- H = HIGH voltage level;
L = LOW voltage level.

ORDERING INFORMATION

TYPE NUMBER	PACKAGE					
	TEMPERATURE RANGE	PINS	PACKAGE	MATERIAL	CODE	MARKING
74AHC2G00DP	-40 to +125 °C	8	TSSOP8	plastic	SOT505-2	A00
74AHCT2G00DP	-40 to +125 °C	8	TSSOP8	plastic	SOT505-2	C00
74AHC2G00DC	-40 to +125 °C	8	VSSOP8	plastic	SOT765-1	A00
74AHCT2G00DC	-40 to +125 °C	8	VSSOP8	plastic	SOT765-1	C00

PINNING

PIN	SYMBOL	DESCRIPTION
1	1A	data input
2	1B	data input
3	2Y	data output
4	GND	ground (0 V)
5	2A	data input
6	2B	data input
7	1Y	data output
8	V _{CC}	supply voltage

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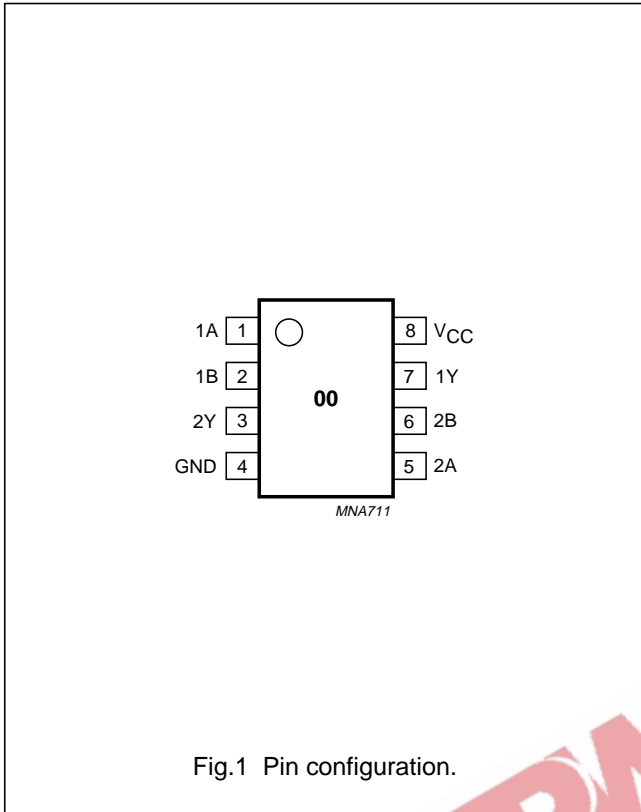


Fig.1 Pin configuration.

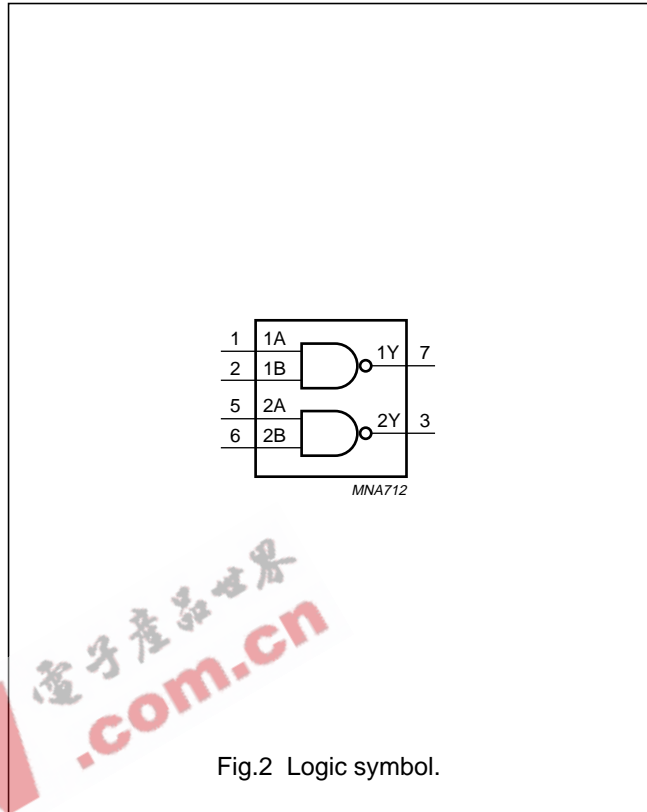


Fig.2 Logic symbol.

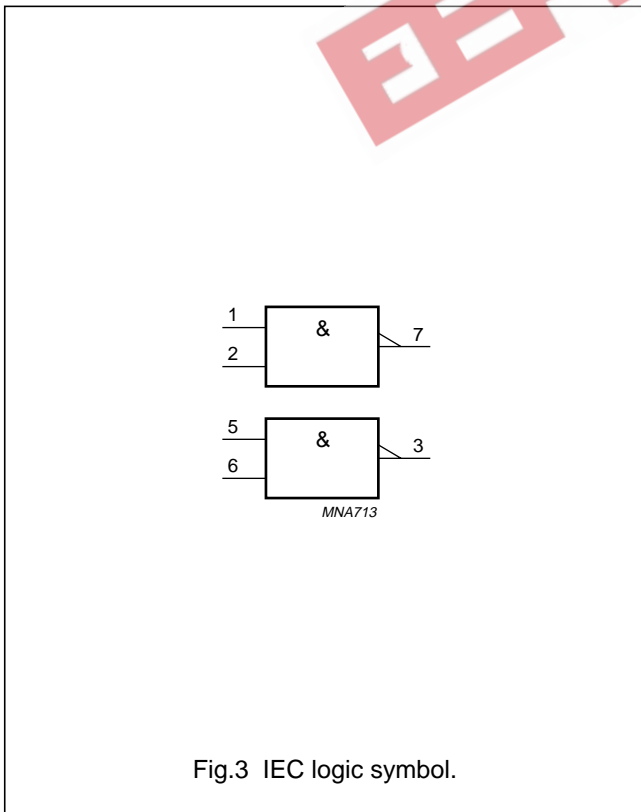


Fig.3 IEC logic symbol.

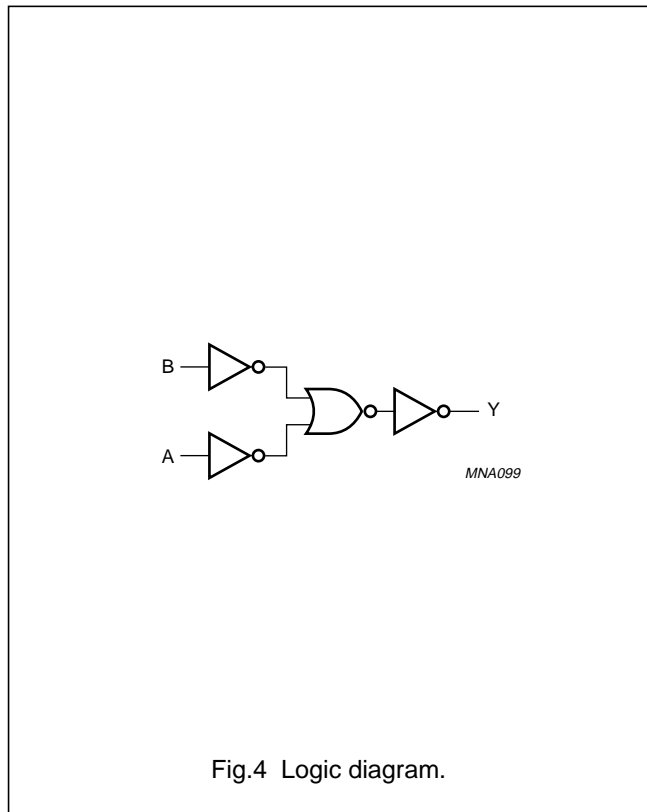


Fig.4 Logic diagram.

2-input NAND gate

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RECOMMENDED OPERATING CONDITIONS

SYMBOL	PARAMETER	CONDITIONS	74AHC2G00			74AHCT2G00			UNIT
			MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
V_{CC}	supply voltage		2.0	5.0	5.5	4.5	5.0	5.5	V
V_I	input voltage		0	–	5.5	0	–	5.5	V
V_O	output voltage		0	–	V_{CC}	0	–	V_{CC}	V
T_{amb}	operating ambient temperature	see DC and AC characteristics per device	–40	+25	+125	–40	+25	+125	°C
t_r, t_f	input rise and fall times	$V_{CC} = 3.3 \pm 0.3$ V	–	–	100	–	–	–	ns/V
		$V_{CC} = 5 \pm 0.5$ V	–	–	20	–	–	20	ns/V

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134); voltages are referenced to GND (ground = 0 V).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CC}	supply voltage		–0.5	+7.0	V
V_I	input voltage		–0.5	+7.0	V
I_{IK}	input diode current	$V_I < -0.5$ V	–	–20	mA
I_{OK}	output diode current	$V_O < -0.5$ V or $V_O > V_{CC} + 0.5$ V; note 1	–	±20	mA
I_O	output source or sink current	-0.5 V < V_O < $V_{CC} + 0.5$ V	–	±25	mA
I_{CC}, I_{GND}	V_{CC} or GND current		–	±75	mA
T_{stg}	storage temperature		–65	+150	°C
P_D	power dissipation	$T_{amb} = -40$ to $+125$ °C	–	250	mW

Note

1. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

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DC CHARACTERISTICS

Type 74AHC2G00

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

SYMBOL	PARAMETER	CONDITIONS		MIN.	TYP.	MAX.	UNIT
		OTHER	V _{CC} (V)				
T_{amb} = 25 °C							
V _{IH}	HIGH-level input voltage		2.0	1.5	–	–	V
			3.0	2.1	–	–	V
			5.5	3.85	–	–	V
V _{IL}	LOW-level input voltage		2.0	–	–	0.5	V
			3.0	–	–	0.9	V
			5.5	–	–	1.65	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL} I _O = –50 µA	2.0	1.9	2.0	–	V
		I _O = –50 µA	3.0	2.9	3.0	–	V
		I _O = –50 µA	4.5	4.4	4.5	–	V
		I _O = –4.0 mA	3.0	2.58	–	–	V
		I _O = –8.0 mA	4.5	3.94	–	–	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL} I _O = 50 µA	2.0	–	0	0.1	V
		I _O = 50 µA	3.0	–	0	0.1	V
		I _O = 50 µA	4.5	–	0	0.1	V
		I _O = 4.0 mA	3.0	–	–	0.36	V
		I _O = 8.0 mA	4.5	–	–	0.36	V
I _{LI}	input leakage current	V _I = V _{CC} or GND	5.5	–	–	0.1	µA
I _{CC}	quiescent supply current	V _I = V _{CC} or GND; I _O = 0	5.5	–	–	10	µA
C _I	input capacitance		–	–	1.5	10	pF

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SYMBOL	PARAMETER	CONDITIONS		MIN.	TYP.	MAX.	UNIT
		OTHER	V _{CC} (V)				
T_{amb} = -40 to +85 °C							
V _{IH}	HIGH-level input voltage		2.0	1.5	–	–	V
			3.0	2.1	–	–	V
			5.5	3.85	–	–	V
V _{IL}	LOW-level input voltage		2.0	–	–	0.5	V
			3.0	–	–	0.9	V
			5.5	–	–	1.65	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL} I _O = -50 µA	2.0	1.9	–	–	V
		I _O = -50 µA	3.0	2.9	–	–	V
		I _O = -50 µA	4.5	4.4	–	–	V
		I _O = -4.0 mA	3.0	2.48	–	–	V
		I _O = -8.0 mA	4.5	3.8	–	–	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL} I _O = 50 µA	2.0	–	–	0.1	V
		I _O = 50 µA	3.0	–	–	0.1	V
		I _O = 50 µA	4.5	–	–	0.1	V
		I _O = 4.0 mA	3.0	–	–	0.44	V
		I _O = 8.0 mA	4.5	–	–	0.44	V
I _{LI}	input leakage current	V _I = V _{CC} or GND	5.5	–	–	1.0	µA
I _{CC}	quiescent supply current	V _I = V _{CC} or GND; I _O = 0	5.5	–	–	10	µA
C _I	input capacitance		–	–	–	10	pF

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SYMBOL	PARAMETER	CONDITIONS		MIN.	TYP.	MAX.	UNIT
		OTHER	V _{CC} (V)				
T_{amb} = -40 to +125 °C							
V _{IH}	HIGH-level input voltage		2.0	1.5	–	–	V
			3.0	2.1	–	–	V
			5.5	3.85	–	–	V
V _{IL}	LOW-level input voltage		2.0	–	–	0.5	V
			3.0	–	–	0.9	V
			5.5	–	–	1.65	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL} I _O = -50 µA	2.0	1.9	–	–	V
		I _O = -50 µA	3.0	2.9	–	–	V
		I _O = -50 µA	4.5	4.4	–	–	V
		I _O = -4.0 mA	3.0	2.40	–	–	V
		I _O = -8.0 mA	4.5	3.70	–	–	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL} I _O = 50 µA	2.0	–	–	0.1	V
		I _O = 50 µA	3.0	–	–	0.1	V
		I _O = 50 µA	4.5	–	–	0.1	V
		I _O = 4.0 mA	3.0	–	–	0.55	V
		I _O = 8.0 mA	4.5	–	–	0.55	V
I _{LI}	input leakage current	V _I = V _{CC} or GND	5.5	–	–	2.0	µA
I _{CC}	quiescent supply current	V _I = V _{CC} or GND; I _O = 0	5.5	–	–	40	µA
C _I	input capacitance		–	–	–	10	pF

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Type 74AHCT2G00

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

SYMBOL	PARAMETER	CONDITIONS		MIN.	TYP.	MAX.	UNIT
		OTHER	V _{CC} (V)				
T_{amb} = 25 °C							
V _{IH}	HIGH-level input voltage		4.5 to 5.5	2.0	–	–	V
V _{IL}	LOW-level input voltage		4.5 to 5.5	–	–	0.8	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL} I _O = –50 µA	4.5	4.4	4.5	–	V
		I _O = –8.0 mA	4.5	3.94	–	–	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL} I _O = 50 µA	4.5	–	0	0.1	V
		I _O = 8.0 mA	4.5	–	–	0.36	V
I _{LI}	input leakage current	V _I = V _{IH} or V _{IL}	5.5	–	–	0.1	µA
I _{CC}	quiescent supply current	V _I = V _{CC} or GND; I _O = 0	5.5	–	–	1.0	µA
ΔI _{CC}	additional quiescent supply current per input pin	V _I = 3.4 V; other inputs at V _{CC} or GND; I _O = 0	5.5	–	–	1.35	mA
C _I	input capacitance			–	1.5	10	pF
T_{amb} = –40 to +85 °C							
V _{IH}	HIGH-level input voltage		4.5 to 5.5	2.0	–	–	V
V _{IL}	LOW-level input voltage		4.5 to 5.5	–	–	0.8	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL} I _O = –50 µA	4.5	4.4	–	–	V
		I _O = –8.0 mA	4.5	3.8	–	–	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL} I _O = 50 µA	4.5	–	–	0.1	V
		I _O = 8.0 mA	4.5	–	–	0.44	V
I _{LI}	input leakage current	V _I = V _{IH} or V _{IL}	5.5	–	–	1.0	µA
I _{CC}	quiescent supply current	V _I = V _{CC} or GND; I _O = 0	5.5	–	–	10	µA
ΔI _{CC}	additional quiescent supply current per input pin	V _I = 3.4 V; other inputs at V _{CC} or GND; I _O = 0	5.5	–	–	1.5	mA
C _I	input capacitance		–	–	–	10	pF

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SYMBOL	PARAMETER	CONDITIONS		MIN.	TYP.	MAX.	UNIT
		OTHER	V _{CC} (V)				
T_{amb} = -40 to +125 °C							
V _{IH}	HIGH-level input voltage		4.5 to 5.5	2.0	–	–	V
V _{IL}	LOW-level input voltage		4.5 to 5.5	–	–	0.8	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}	4.5	4.4	–	–	V
		I _O = -50 μA I _O = -8.0 mA	4.5	3.70	–	–	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}	4.5	–	–	0.1	V
		I _O = 50 μA I _O = 8.0 mA	4.5	–	–	0.55	V
I _{LI}	input leakage current	V _I = V _{IH} or V _{IL}	5.5	–	–	2.0	μA
I _{CC}	quiescent supply current	V _I = V _{CC} or GND; I _O = 0	5.5	–	–	40	μA
ΔI _{CC}	additional quiescent supply current per input pin	V _I = 3.4 V; other inputs at V _{CC} or GND; I _O = 0	5.5	–	–	1.5	mA
C _I	input capacitance		–	–	–	10	pF

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AC CHARACTERISTICS

Type 74AHC2G00

GND = 0 V; $t_r = t_f \leq 3.0$ ns.

SYMBOL	PARAMETER	TEST CONDITIONS			MIN.	TYP.	MAX.	UNIT
		WAVEFORMS	C_L (pF)	V_{CC} (V)				
$T_{amb} = 25\text{ }^\circ\text{C}$								
t_{PHL}/t_{PLH}	propagation delay input nA and nB to output nY	see Figs 5 and 6	15	3.0 to 3.6	–	4.5 ⁽¹⁾	7.9	ns
				4.5 to 5.5	–	3.5 ⁽²⁾	5.5	ns
		50	3.0 to 3.6	–	6.5 ⁽¹⁾	11.4	ns	
			4.5 to 5.5	–	4.9 ⁽²⁾	7.5	ns	
$T_{amb} = -40\text{ to }+85\text{ }^\circ\text{C}$								
t_{PHL}/t_{PLH}	propagation delay input nA and nB to output nY	see Figs 5 and 6	15	3.0 to 3.6	1.0	–	9.5	ns
				4.5 to 5.5	1.0	–	6.5	ns
		50	3.0 to 3.6	1.0	–	13.0	ns	
			4.5 to 5.5	1.0	–	8.5	ns	
$T_{amb} = -40\text{ to }+125\text{ }^\circ\text{C}$								
t_{PHL}/t_{PLH}	propagation delay input nA and nB to output nY	see Figs 5 and 6	15	3.0 to 3.6	1.0	–	10.5	ns
				4.5 to 5.5	1.0	–	7.0	ns
		50	3.0 to 3.6	1.0	–	14.5	ns	
			4.5 to 5.5	1.0	–	9.5	ns	

Notes

1. Typical values are measured at $V_{CC} = 3.3$ V.
2. Typical values are measured at $V_{CC} = 5.0$ V.

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Type 74AHCT2G00GND = 0 V; $t_r = t_f \leq 3.0$ ns.

SYMBOL	PARAMETER	TEST CONDITIONS			MIN.	TYP.	MAX.	UNIT
		WAVEFORMS	C_L (pF)	V_{CC} (V)				
$T_{amb} = 25\text{ }^\circ\text{C}$								
t_{PHL}/t_{PLH}	propagation delay input nA and nB to output nY	see Figs 5 and 6	15	4.5 to 5.5	1.0	3.6 ⁽¹⁾	6.2	ns
			50	4.5 to 5.5	1.0	5.0 ⁽¹⁾	7.9	ns
$T_{amb} = -40\text{ to }+85\text{ }^\circ\text{C}$								
t_{PHL}/t_{PLH}	propagation delay input nA and nB to output nY	see Figs 5 and 6	15	4.5 to 5.5	1.0	–	7.1	ns
			50	4.5 to 5.5	1.0	–	9.0	ns
$T_{amb} = -40\text{ to }+125\text{ }^\circ\text{C}$								
t_{PHL}/t_{PLH}	propagation delay input nA and nB to output nY	see Figs 5 and 6	15	4.5 to 5.5	1.0	–	8.0	ns
			50	4.5 to 5.5	1.0	–	10.0	ns

Note

- Typical values are measured at $V_{CC} = 5.0$ V.

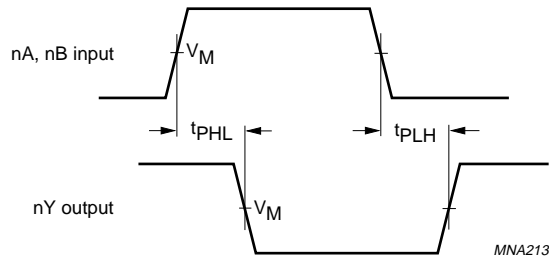


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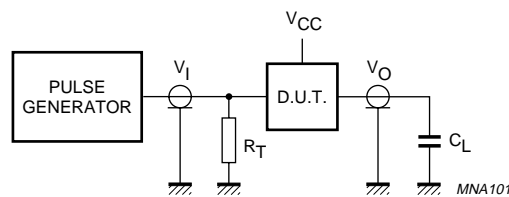
74AHC2G00; 74AHCT2G00

AC WAVEFORMS



FAMILY	V _M INPUT	V _M OUTPUT
AHC2G00	50% V _{CC}	50% V _{CC}
AHCT2G00	1.5 V	50% V _{CC}

Fig.5 The inputs (nA and nB) to output (nY) propagation delays.



FAMILY	V _I INPUT REQUIREMENTS
AHC2G00	GND to V _{CC}
AHCT2G00	GND to 3.0 V

Definitions for test circuit:

C_L = Load capacitance including jig and probe capacitance (See "AC characteristics" for the value).

R_T = Termination resistance should be equal to the output impedance Z₀ of the pulse generator.

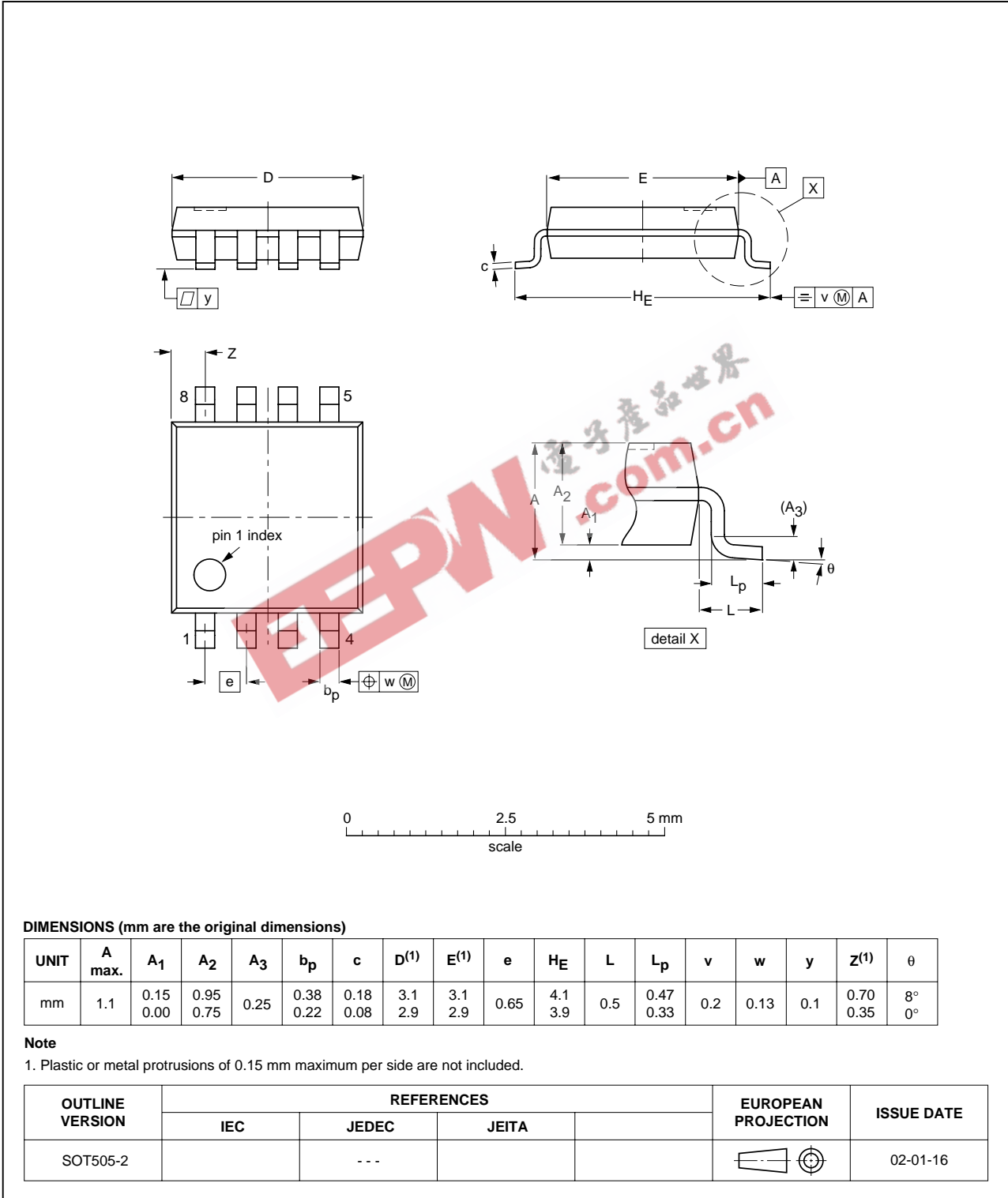
Fig.6 Load circuitry for switching times.

2-input NAND gate

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PACKAGE OUTLINES

TSSOP8: plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm SOT505-2

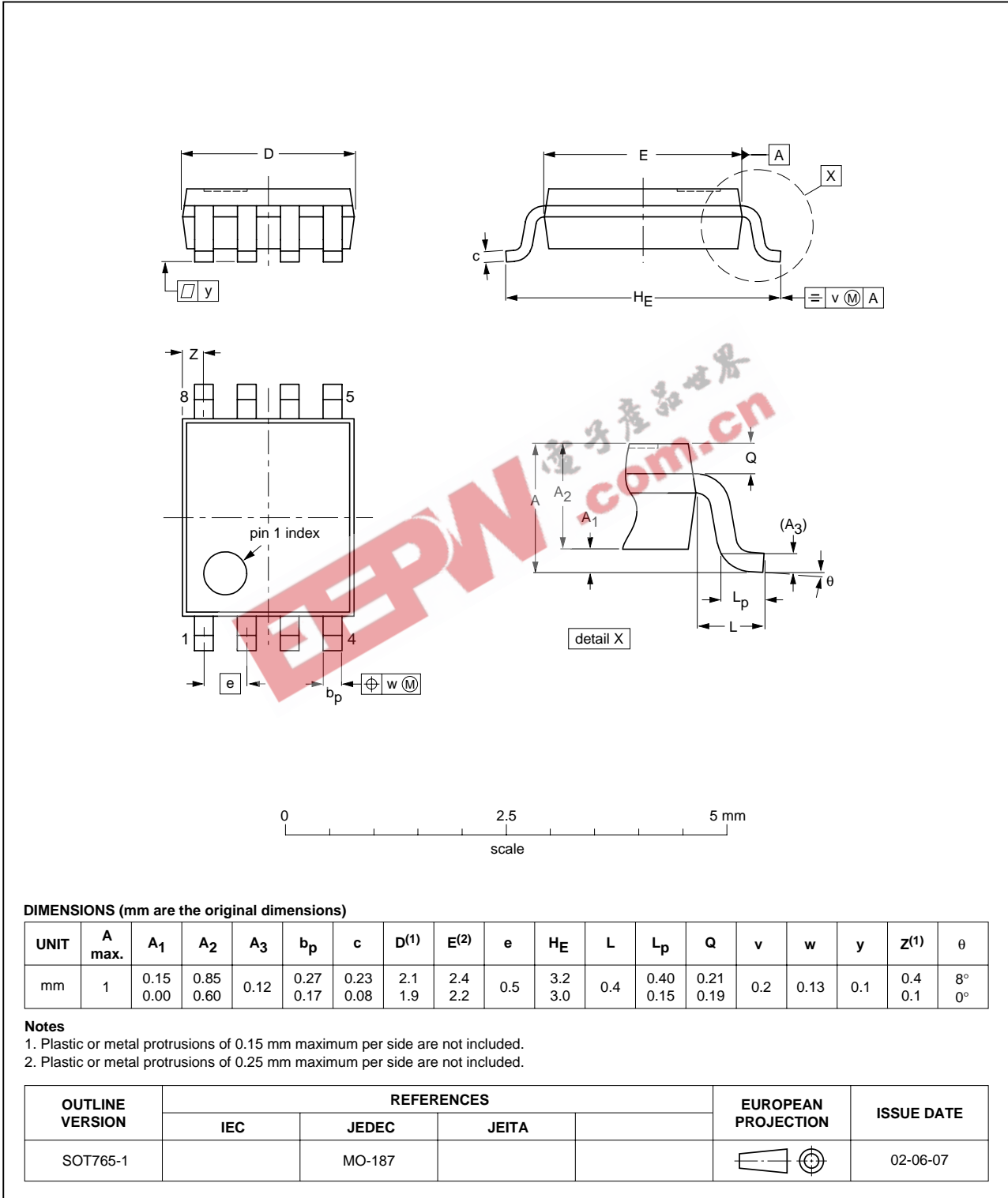


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VSSOP8: plastic very thin shrink small outline package; 8 leads; body width 2.3 mm

SOT765-1



2-input NAND gate

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DATA SHEET STATUS

LEVEL	DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾⁽³⁾	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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